

DDR Termination Regulator

General Description

The RTQ2508 is a sink/source tracking termination regulator. It is specifically designed for low-cost and low-external component count systems. The RTQ2508 possesses a high speed operating amplifier that provides fast load transient response and only requires a minimum $10\mu F \times 3$ ceramic output capacitor. The RTQ2508 supports remote sensing functions and all features required to power the DDRIII and Low Power DDRIII / DDRIV VTT bus termination according to the JEDEC specification. In addition, the RTQ2508 provides an open-drain PGOOD signal to monitor the output regulation and an EN signal that can be used to discharge VTT during S3 (suspend to RAM) for DDR applications.

The RTQ2508 is available in the thermal efficient package, WDFN-10L 3x3.

Features

VIN Input Voltage Range: 1.1V to 3.5V
VCNTL Input Voltage Range: 2.9V to 5.5V

• Support Ceramic Capacitors

• Power Good Indicator

• 10mA Source/Sink Reference Output

• Meet DDRI, DDRII JEDEC Spec

 Support DDRI, DDRII, DDRIII and Low Power DDRIII/ DDRIV VTT Applications

• Soft-Start Function

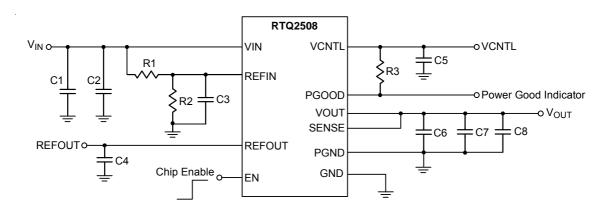
UVLO and OCP Protection

• Thermal Shutdown

Applications

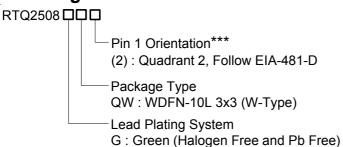
- Notebook/Desktop/Server
- Telecom/Datacom, GSM Base Station, LCD-TV/PDP-TV, Copier/Printer, Set-Top Box

Simplified Application Circuit





Ordering Information



Pin Configuration

(TOP VIEW) VCNTL
PGOOD
GOOD
COORD
C REFIN 1 VIN 2 VOUT 3 PGND 4. SENSE 5

WDFN-10L 3x3

Note:

***Empty means Pin1 orientation is Quadrant 1 Richtek products are:

- ▶ RoHS compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.
- ▶ Suitable for use in SnPb or Pb-free soldering processes.

Marking Information



R8=: Product Code YMDNN: Date Code

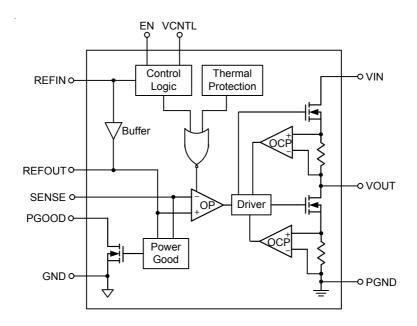
Functional Pin Description

Pin No.	Pin Name	Pin Function					
1	REFIN	Reference input.					
2	VIN	Power input of the regulator.					
3	VOUT	wer output of the regulator.					
4	PGND	Power ground of the regulator.					
5	SENSE	Voltage sense input for the regulator. Connect to positive terminal of the output capacitor or the load.					
6	REFOUT	Reference output. Connect to GND through a 0.1µF ceramic capacitor.					
7	EN	Enable control input. For DDR VTT application, connect EN to SLP_S3. other applications, use EN as the ON/OFF function.					
9	PGOOD	Power good open-drain output. Connect a pull-up resistor between this pin and VCNTL pin.					
10	VCNTL	Control voltage input. Connect this pin to the 3.3V or 5V power supply. A ceramic decoupling capacitor with a value between $1\mu F$ and $4.7\mu F$ is required.					
8	GND	Analog ground. Connect to negative terminal of the output capacitor.					
11 (Exposed Pad)	PAD	Exposed pad. The exposed pad is internally unconnected and must be soldered to a large PGND plane. Connect this PGND plane to other layers with thermal vias to help dissipate heat from the device.					

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Functional Block Diagram



Operation

The RTQ2508 is a linear sink/source DDR termination regulator with current capability up to 3A. The RTQ2508 builds in a high-side N-MOSFET which provides current sourcing and a low-side N-MOSFET which provides current sinking. All the control circuits are supplied by the power VCNTL. In normal operation, the error amplifier OP adjusts the gate driving voltage of the power MOSFET to achieve SENSE voltage well tracking the REFIN voltage.

Both the source and sink currents are detected by the internal sensing resistor, and the OCP function will work to limit the current to a designed value when overload happens. Furthermore, the current will be folded back to be one half if VOUT is out of the power good window.

Buffer

This function provides REFOUT output equal to V_{REFIN} with 10mA source/sink current capability.

Power Good

When the SENSE voltage is in the power good window and lasts for a certain delay time, then the PGOOD pin will be high impedance and the PGOOD voltage will be pulled high by the external resistor.

Over-Current Protection

The device continuously monitors the output current to protect the pass transistor against abnormal operations. The current limit (I_{LIM}) level reduces by one-third when the output voltage is not within the powergood window. This reduction is a non-latch protection.

Control Logic

This block includes VCNTL UVLO, REFIN UVLO and Enable/Disable functions, and provides logic control to the whole chip.

Thermal Protection

Both the high-side and low-side power MOSFETs will be turned off when the junction temperature is higher than typically 160°C, and be released to normal operation when junction temperature falls below 120°C typically.

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Absolute Maximum Ratings (Note 1)

• Input Voltage, EN, REFIN, SENSE	-0.3V to 6V
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Output Voltage, VOUT, REFOUT, PGOOD	–0.3V to 6V
 Power Dissipation, P_D @ T_A = 25°C 	
WDFN-10L 3x3 2	2.5W
Package Thermal Resistance (Note 2)	
WDFN-10L 3x3, θ_{JA} 4	10°C/W
WDFN-10L 3x3, θ_{JC} 7	7.5°C/W
• Lead Temperature (Soldering, 10 sec.) 2	260°C
• Junction Temperature 1	150°C
• Storage Temperature Range	–65°C to 150°C
ESD Susceptibility (Note 3)	
HBM (Human Body Model) 2	2kV
Recommended Operating Conditions (Note 4)	
Control Input Voltage, VCNTL 2	2.9V to 5.5V

Electrical Characteristics

 $(V_{IN} = 1.5V, V_{EN} = V_{CNTL} = 3.3V, V_{REFIN} = V_{SENSE} = 0.75V, C_{OUT} = 10 \mu F x 3, T_{J} = -40 ^{\circ}C$ to 85 °C, unless otherwise specified)

• Supply Input Voltage, VIN ------ 1.1V to 3.5V • Junction Temperature Range ----- --- -40°C to 125°C

Parameter	Symbol	Test Conditions		Тур	Max	Unit			
Supply Current									
VCNTL Supply Current	I _{VCNTL}	V _{EN} = V _{CNTL} , no load		0.7	1	mA			
VCNTL Shutdown Current	ISHDN_VCNTL	V _{EN} = 0V, V _{REFIN} = 0V, no load		65	80	μА			
VCNTE SHULLOWN CUITER		V _{EN} = 0V, V _{REFIN} > 0.4V, no load		200	400				
VIN Supply Current	I _{VIN}	V _{EN} = V _{CNTL} , no load		1	50	μΑ			
VIN Shutdown Current I _{SHDN_VIN}		V _{EN} = 0V, no load		0.1	50	μА			
Output									
	V _О UТО	$V_{IN} = 1.5V$, $V_{REFIN} = 0.75V$, $I_{OUT} = 0A$		0.75					
VTT Output Voltage		$V_{IN} = 1.35V$, $V_{REFIN} = 0.675V$, $I_{OUT} = 0A$		0.675		٧			
		V_{IN} = 1.2V, V_{REFIN} = 0.6V, I_{OUT} = 0A		0.6					
	set V _{OUT_} os	I _{OUT} < ±2A, V _{LDOIN} = 1.5V, V _{OUT_OS} = V _{OUT} - V _{OUTO}	-25		25				
VTT Output Voltage Offset		I _{OUT} < ±2A, V _{LDOIN} = 1.35V, V _{OUT_OS} = V _{OUT} - V _{OUTO}	-25		25	mV			
		I _{OUT} < ±2A, V _{LDOIN} = 1.2V, V _{OUT} _{OS} = V _{OUT} - V _{OUT} O	-25		25				



Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
VOUT Source Current Lim	it I _{LIM_VOUT_SR}	VOUT in PGOOD window	3	4.5		Α	
VOUT Sink Current Limit	ILIM_VOUT_SK	VOUT in PGOOD window	3	4.5		Α	
VOUT Discharge Resistance	RDISCHARGE	$V_{REFIN} = 0V$, $V_{OUT} = 0.3V$, $V_{EN} = 0V$		18	25	Ω	
Power Good Comparato	r						
		V _{SENSE} lower threshold with respect to REFOUT		-20			
PGOOD Threshold	V _{TH_PGOOD}	V _{SENSE} upper threshold with respect to REFOUT		20		%	
		PGOOD hysteresis	I	5			
PGOOD Start-Up Delay	T _{PGDELAY1}	Start-up rising delay, VSENSE within PGOOD range	1	2		ms	
Output Low Voltage	VLOW_PGOOD	IPGOOD = 4mA			0.4	V	
PGOOD Falling Delay	T _{PGDELAY2}	Falling delay, V _{SENSE} is out of PGOOD range	-	10		μS	
Leakage Current	ILEAKAGE _PGOOD	V _{SENSE} = V _{REFIN} (PGOOD high impedance), V _{PGOOD} = V _{CNTL} + 0.2V			1	μА	
REFIN and REFOUT							
REFIN Input Current	I _{REFIN}	VEN = VCNTL			1	μΑ	
REFIN Voltage Range	VREFIN		0.5		1.8	V	
REFIN Under-Voltage	Vuvlo_refin	REFIN rising	360	390	420	mV	
Lockout	VUVLO_REFIN	Hysteresis		20			
		-10mA < I _{REFOUT} < 10mA, V _{REFIN} = 0.75V	-15		15		
REFOUT Voltage Tolerand to VREFIN	V _{TOL_REFOUT}	-10mA < I _{REFOUT} < 10 mA, V _{REFIN} = 0.675 V	-15		15	mV	
		-10mA < I _{REFOUT} < 10mA, V _{REFIN} = 0.6V	-15		15		
REFOUT Source Current Limit	ILIM_REFOUT_SR	VREFOUT = 0V	10	40		mA	
REFOUT Sink Current Lin	nit ILIM_REFOUT_SK	V _{REFOUT} = REFIN + 1V	10	40		mA	
UVLO/EN							
UVLO Threshold	VUVLO_VCNTL	Rising	2.5	2.7	2.85	V	
OVEO TITOGNOIO	VOVEO_VOIVIE	Hysteresis		120		mV	
EN Input Logic-Hig	n V _{IN_H}		1.7			_V	
Voltage Logic-Low	VIN_L	V _{IN_L}			0.3		
Thermal Shutdown			•				
Thermal Shutdown	T _{SD}	Shutdown temperature (Note 5)		160		°C	
Threshold	1.05	Hysteresis (Note 5)		15			



- Note 1. Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.
- Note 2. θ_{JA} is measured under natural convection (still air) at $T_A = 25^{\circ}C$ with the component mounted on a high effectivethermal-conductivity four-layer test board on a JEDEC 51-7 thermal measurement standard. θ_{JC} is measured at the exposed pad of the package.
- Note 3. Devices are ESD sensitive. Handling precaution is recommended.
- Note 4. The device is not guaranteed to function outside its operating conditions.
- Note 5. Guarantee by design.



Typical Application Circuit

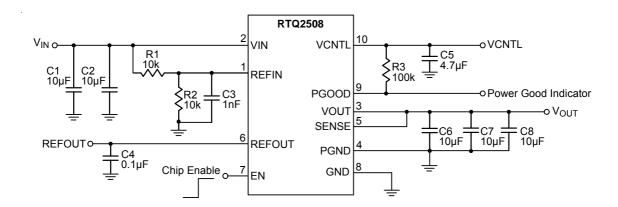
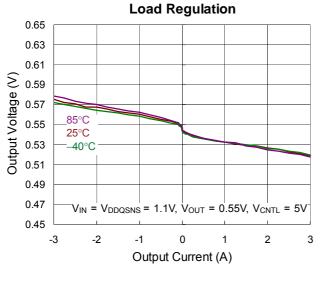


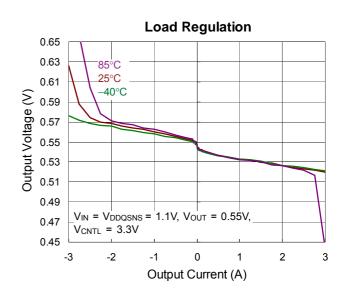
Table 1. Recommended External Components

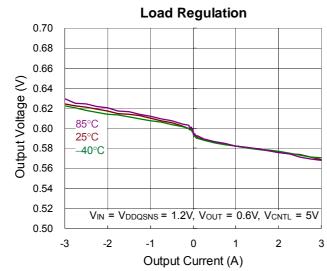
Component	Description	Vendor P/N			
C1, C2, C6, C7, C8	10μF, 6.3V, X7R, 0805	GRM21BR70J106KE76L (Murata) CGA4J1X7R0J106K125AC (TDK)			
C3	1nF, 50V, X7R, 0603	GCD188R71H102KA01D (Murata) CGA3E2X7R1H102K080AA (TDK)			
C4	0.1μF, 16V, X7R, 0603	GCJ188R71C104KA01D (Murata)			
C5	4.7μF, 6.3V, X5R, 0603	GRT188R60J475ME01D (Murata) CGB3B3X5R0J475M055AB(TDK)			

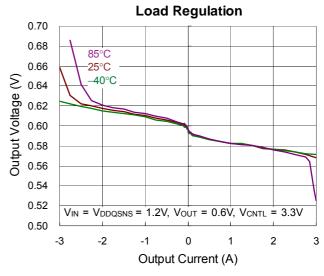


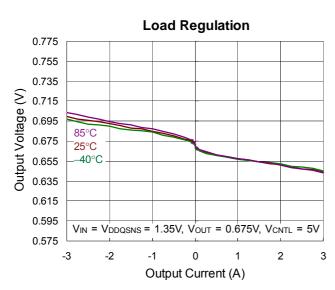
Typical Operating Characteristics

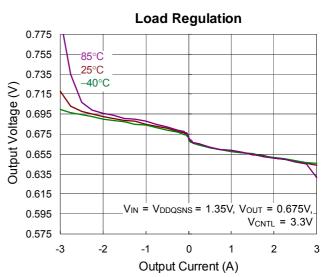






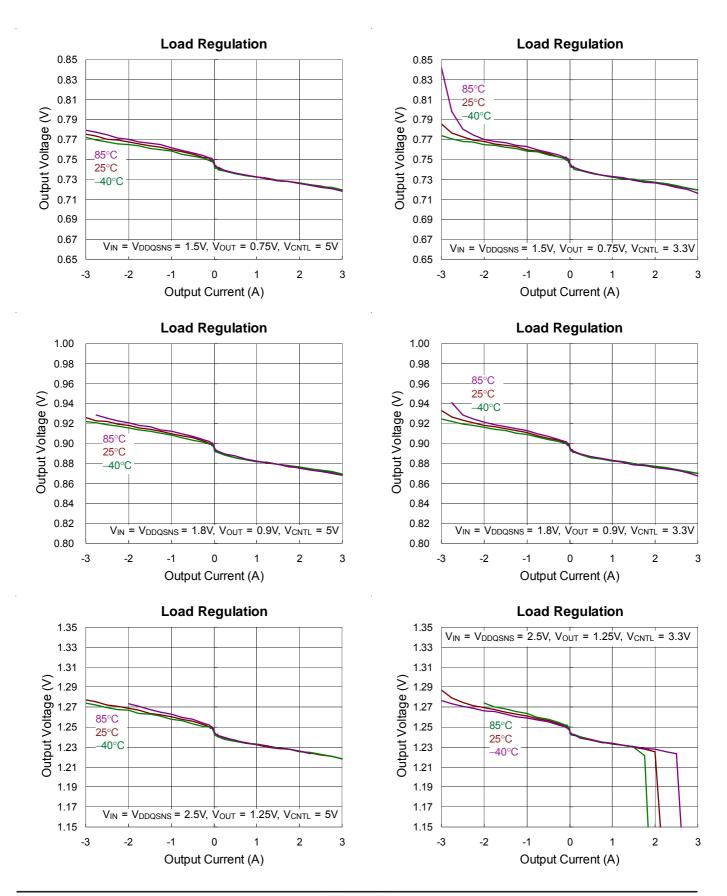




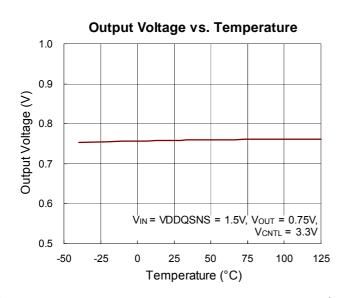


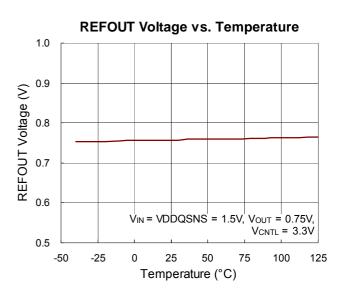
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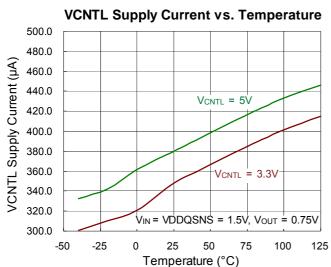


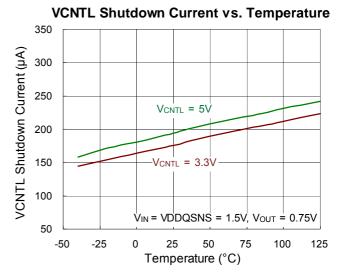


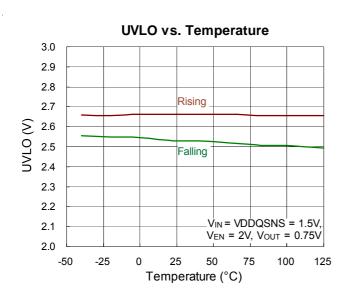


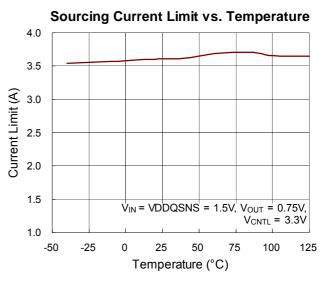




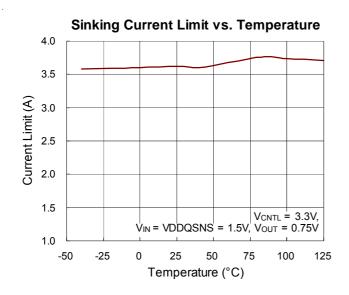


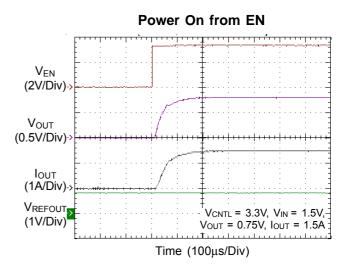


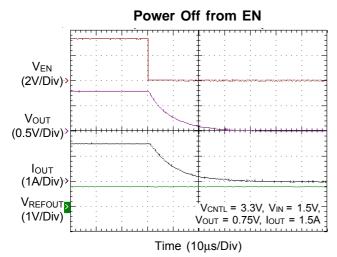


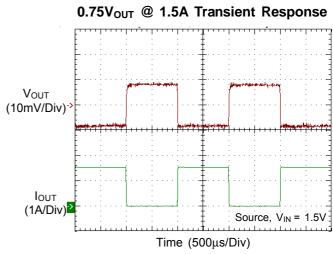


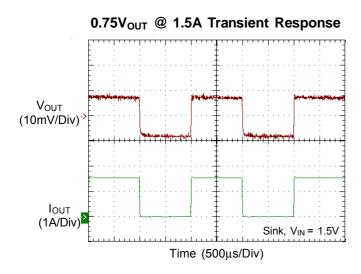














Application Information

The RTQ2508 is a 3A sink/source tracking termination regulator. It is specifically designed for low-cost and lowexternal component count system such as notebook PC applications. The RTQ2508 possesses a high speed operating amplifier that provides fast load transient response.

Capacitor Selection

Good bypassing is recommended from VIN to GND to help improve AC performance. A 10µF or greater input capacitor located as close as possible to the IC is recommended. The input capacitor must be located at a distance of less than 0.5 inches from the VIN pin of the IC.

Adding a 1µF ceramic capacitor close to the VCNTL pin and it should be kept away from any parasitic impedance from the supply power. For stable operation, the total capacitance of the ceramic capacitor at the output terminal must be larger than 30µF. The RTQ2508 is designed specifically to work with low ESR ceramic output capacitor in space saving and performance consideration. Larger output capacitance can reduce the noise and improve load transient response, stability and PSRR. The output capacitor should be located near the VOUT pin as close as possible.

Thermal Considerations

The junction temperature should never exceed the absolute maximum junction temperature T_{J(MAX)}, listed under Absolute Maximum Ratings, to avoid permanent damage to the device. The maximum allowable power dissipation depends on the thermal resistance of the IC package, the PCB layout, the rate of surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation can be calculated using the following formula:

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

where $T_{J(MAX)}$ is the maximum junction temperature, T_A is the ambient temperature, and θ_{JA} is the junction-to-ambient thermal resistance.

For continuous operation, the maximum operating junction temperature indicated under Recommended Operating Conditions is 125°C. The junction-to-ambient thermal resistance, θ_{JA} , is highly package dependent. For a WDFN-10L 3x3 package, the thermal resistance, θ_{JA} , is 40°C/W on a standard JEDEC 51-7 high effective-thermalconductivity four-layer test board. The maximum power dissipation at T_A = 25°C can be calculated as below:

 $P_{D(MAX)} = (125^{\circ}C - 25^{\circ}C) / (40^{\circ}C/W) = 2.5W$ for a WDFN-10L 3x3 package.

The maximum power dissipation depends on the operating ambient temperature for the fixed $T_{J(MAX)}$ and the thermal resistance, θ_{JA} . The derating curves in Figure 1 allows the designer to see the effect of rising ambient temperature on the maximum power dissipation.

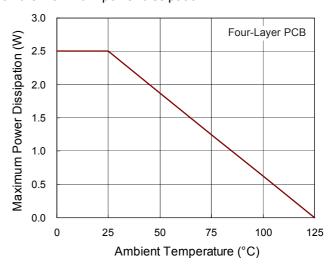


Figure 1. Derating Curve of Maximum Power Dissipation

Layout Considerations

For best performance of the RTQ2508, the PCB layout suggestions below are highly recommend:

- With wide and short connection plane between capacitors and pins for trace impedance minimization.
- > The ground plane connected by a wide copper surface for good thermal dissipation, add via connection also helps reduce the GND loop trace.
- Connect the SENSE pin to the positive node of output capacitor at V_{OUT} terminal for output target level remote sensing.



Since the output voltage V_{OUT} setting is follow the REFIN pin input voltage level V_{REFIN} (V_{OUT} = V_{REFIN}), the REFIN pin can connected with independent voltage source for stable input signal and good V_{OUT} target accuracy. For the application which V_{REFIN} sinks the voltage source divided from VIN power trace, with separate connection trace between R1 and VIN terminal side for good V_{REFIN} signal stability also avoid the reference voltage level shrink down caused by V_{IN} trace loss at high load operation.

Figure 2 shows an example for the layout reference that reduce conduction trace loop, helping inductive parasitic minimize, load transient reduction and good circuit stability.

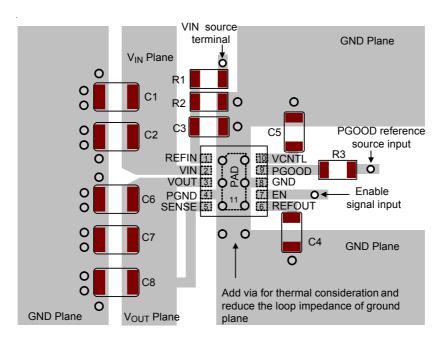
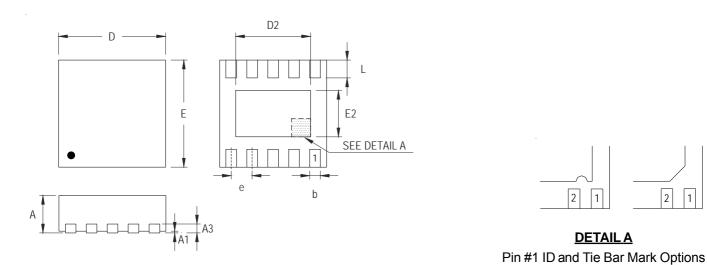


Figure 2. PCB Layout Guide



Outline Dimension



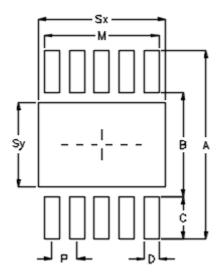
Note: The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

Symbol	Dimensions I	n Millimeters	Dimensions In Inches			
	Min	Max	Min	Max		
Α	0.700	0.800	0.028	0.031		
A1	0.000	0.050	0.000	0.002		
A3	0.175	0.250	0.007	0.010		
b	0.180	0.300	0.007	0.012		
D	2.950	3.050	0.116	0.120		
D2	2.300	2.650	0.091	0.104		
Е	2.950	3.050	0.116	0.120		
E2	1.500	1.750	0.059	0.069		
е	0.5	500	0.0)20		
L	0.350	0.450	0.014	0.018		

W-Type 10L DFN 3x3 Package



Footprint Information



Package	Number of	Footprint Dimension (mm)							Tolerance	
	Pin	Р	Α	В	С	D	Sx	Sy	М	Tolerance
V/W/U/X/ZDFN3*3-10	10	0.50	3.80	2.10	0.85	0.30	2.55	1.70	2.30	±0.05

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